

0.8A, 200V, 0.800 Ohm, N-Channel Power MOSFET

This N-Channel enhancement mode silicon gate power field effect transistor is an advanced power MOSFET designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching convertors, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Formerly developmental type TA09600.

Ordering Information

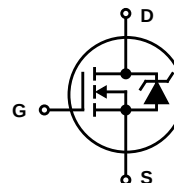
PART NUMBER	PACKAGE	BRAND
IRFD220	HEXDIP	IRFD220

NOTE: When ordering, use the entire part number.

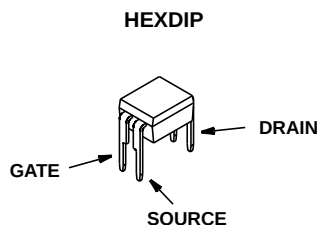
Features

- 0.8A, 200V
- $r_{DS(ON)} = 0.800\Omega$
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging



Absolute Maximum Ratings

$T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

	IRFD220	UNITS
Drain to Source Breakdown Voltage (Note 1)	V_{DS} 200	V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	V_{DGR} 200	V
Continuous Drain Current	I_D 0.8	A
Pulsed Drain Current (Note 3)	I_{DM} 6.4	A
Gate to Source Voltage	V_{GS} ± 20	V
Maximum Power Dissipation	P_D 1.0	W
Linear Derating Factor (See Figure 1)	0.008	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy Rating (Note 4)	E_{AS} 85	mJ
Operating and Storage Temperature	T_J, T_{STG} -55 to 150	$^{\circ}\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	T_L 300	$^{\circ}\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg} 260	$^{\circ}\text{C}$

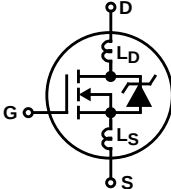
CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

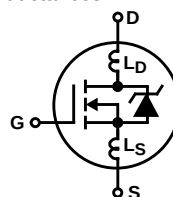
NOTE:

1. $T_J = 25^{\circ}\text{C}$ to $T_J = 125^{\circ}\text{C}$.

Electrical Specifications

$T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V (Figure 9)		200	-	-	V
Gate to Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA		2.0	-	4.0	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = Rated BV _{DSS} , V _{GS} = 0V		-	-	25	μA
		V _{DS} = 0.8 x Rated BV _{DSS} , V _{GS} = 0V, T _C = 125 ⁰ C		-	-	250	μA
On-State Drain Current (Note 2)	I _{D(ON)}	V _{DS} > I _{D(ON)} x r _{DS(ON)MAX} , V _{GS} = 10V (Figure 6)		0.8	-	-	A
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V		-	-	±100	nA
Drain to Source On Resistance (Note 2)	r _{DS(ON)}	I _D = 0.4A, V _{GS} = 10V (Figures 7, 8)		-	0.5	0.8	Ω
Forward Transconductance (Note 2)	g _{fs}	V _{DS} > I _{D(ON)} x r _{DS(ON)MAX} , I _D = 0.4A (Figure 11)		0.5	1.1	-	S
Turn-On Delay Time	t _{d(ON)}	V _{DD} = 0.5 x Rated BV _{DSS} , I _D ≈ 0.8A, R _G = 9.1Ω, R _L = 74Ω, V _{GS} = 10V, MOSFET Switching Times are Essentially Independent of Operating Temperature		-	20	40	ns
Rise Time	t _r			-	30	60	ns
Turn-Off Delay Time	t _{d(OFF)}			-	50	100	ns
Fall Time	t _f			-	30	60	ns
Total Gate Charge (Gate to Source + Gate to Drain)	Q _{g(TOT)}	V _{GS} = 10V, I _D ≈ 0.8A, V _{DS} = 0.8 x Rated BV _{DSS} I _{G(REF)} = 1.5mA, (Figure 13) Gate Charge is Essentially Independent of Operating Temperature		-	11	15	nC
Gate to Source Charge	Q _{gs}			-	6.0	-	nC
Gate to Drain “Miller” Charge	Q _{gd}			-	5.0	-	nC
Input Capacitance	C _{ISS}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz (Figure 10)		-	450	-	pF
Output Capacitance	C _{OSS}			-	150	-	pF
Reverse Transfer Capacitance	C _{RSS}			-	40	-	pF
Internal Drain Inductance	L _D	Measured from the Drain Lead, 2mm (0.08in) from Package to Center of Die	Modified MOSFET Symbol Showing the Internal Devices Inductances 	-	4.0	-	nH
Internal Source Inductance	L _S	Measured from the Source Lead, 2mm (0.08in) from Header to Source Bonding Pad		-	6.0	-	nH
Thermal Resistance Junction to Ambient	R _{θJA}	Free Air Operation		-	-	120	⁰ C/W



Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Continuous Source to Drain Current	I_{SD}	Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Diode	-	-	0.8	A
Pulse Source to Drain Current (Note 3)	I_{SDM}		-	-	6.4	A
Source to Drain Diode Voltage (Note 2)	V_{SD}	$T_J = 25^{\circ}\text{C}$, $I_{SD} = 0.8\text{A}$, $V_{GS} = 0\text{V}$ (Figure 12)	-	-	2.0	V
Reverse Recovery Time	t_{rr}	$T_J = 150^{\circ}\text{C}$, $I_{SD} = 0.8\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	150	-	ns
Reverse Recovery Charge	Q_{RR}	$T_J = 150^{\circ}\text{C}$, $I_{SD} = 0.8\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	0.6	-	μC

NOTES:

2. Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. Repetitive rating: pulse width limited by Max junction temperature.
4. $V_{DD} = 25\text{V}$, starting $T_J = 25^{\circ}\text{C}$, $L = 12.62\text{mH}$, $R_G = 50\Omega$, peak $I_{AS} = 3.5\text{A}$.

Typical Performance Curves Unless Otherwise Specified

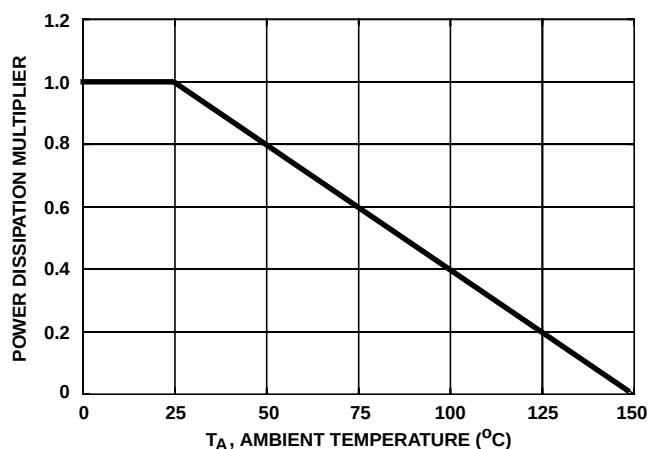


FIGURE 1. NORMALIZED POWER DISSIPATION vs AMBIENT TEMPERATURE

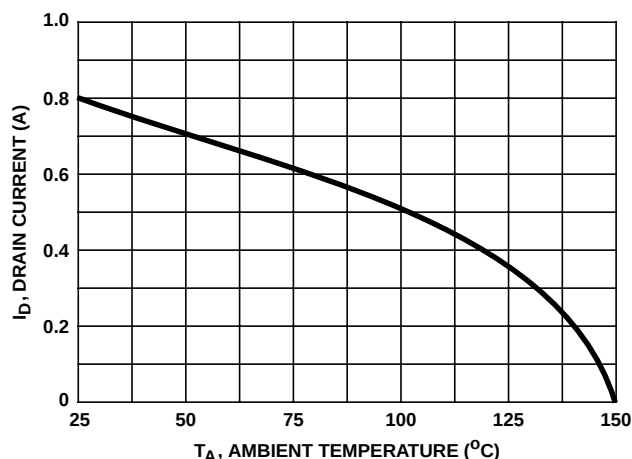


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs AMBIENT TEMPERATURE

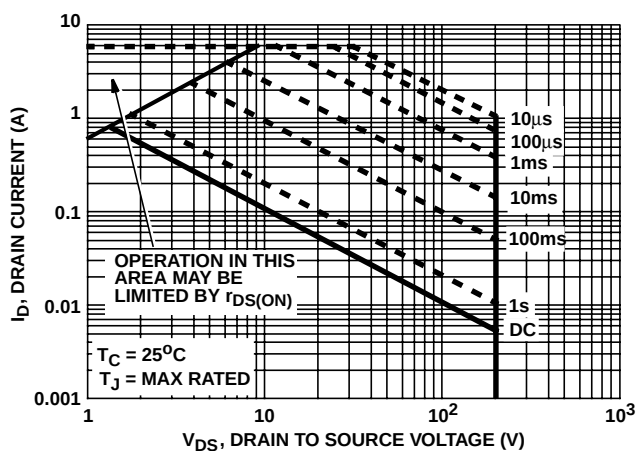


FIGURE 3. FORWARD BIAS SAFE OPERATING AREA

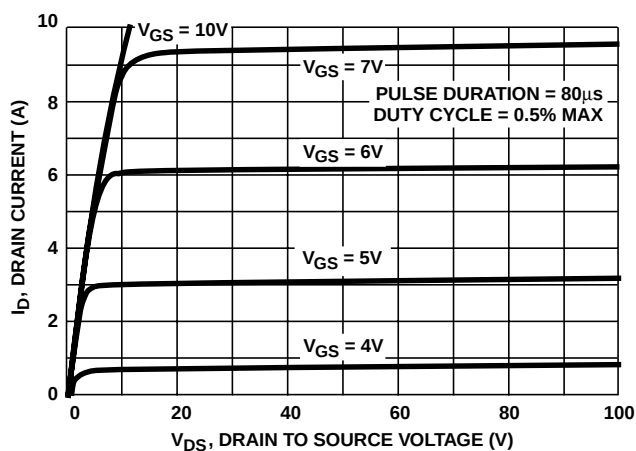


FIGURE 4. OUTPUT CHARACTERISTICS

Typical Performance Curves Unless Otherwise Specified (Continued)

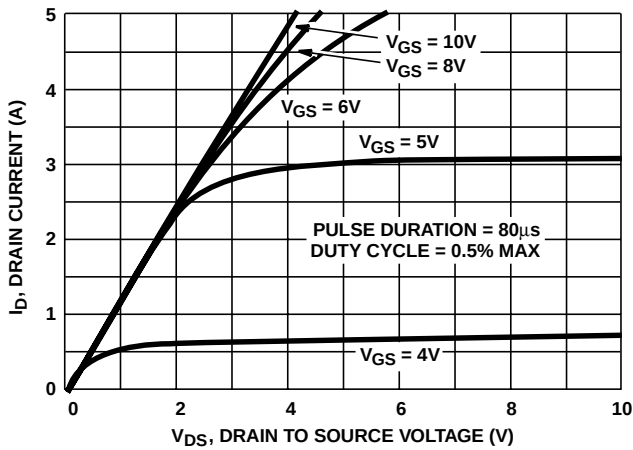


FIGURE 5. SATURATION CHARACTERISTICS

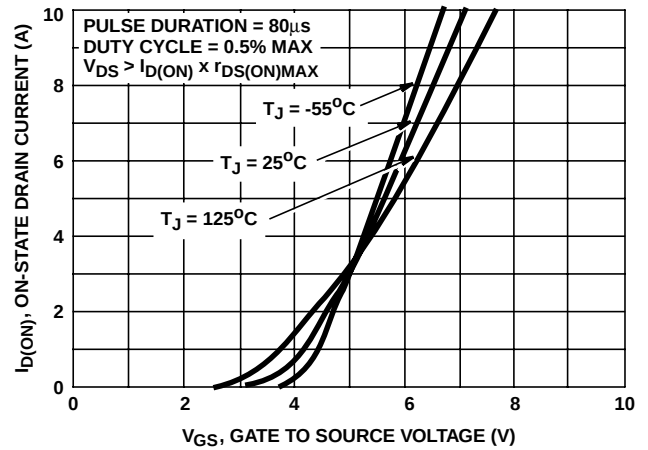


FIGURE 6. TRANSFER CHARACTERISTICS

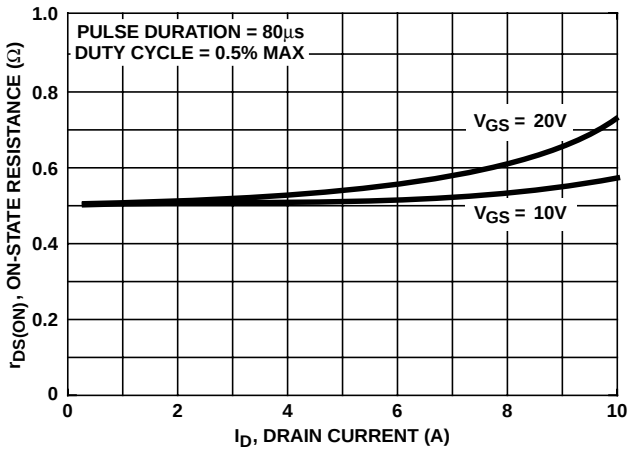


FIGURE 7. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

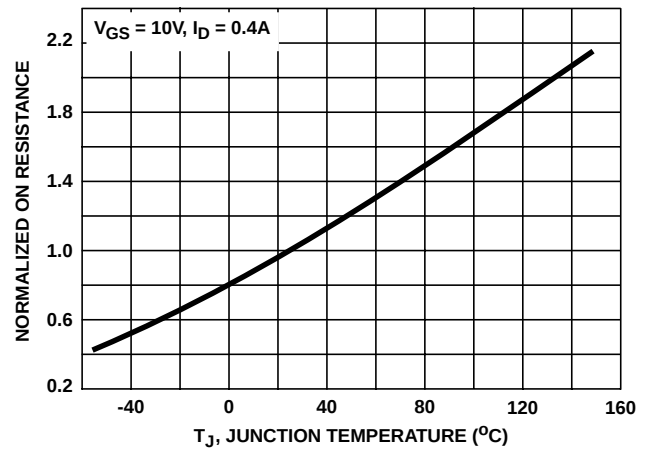


FIGURE 8. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

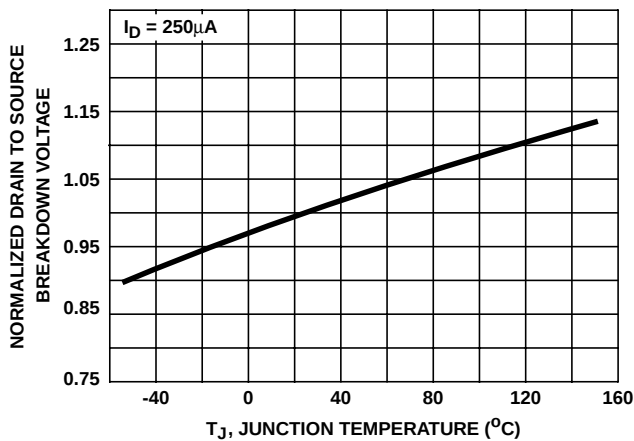


FIGURE 9. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

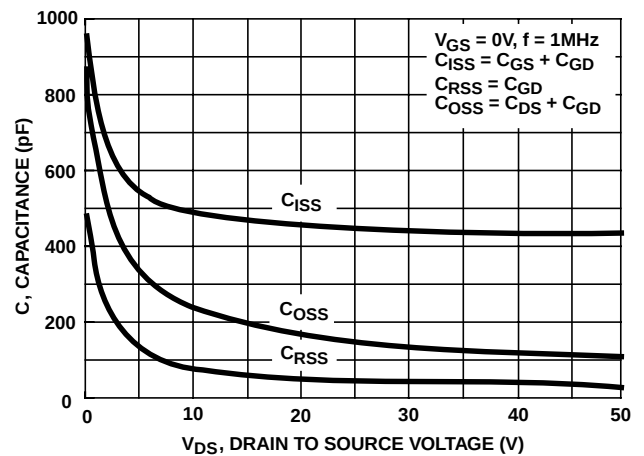


FIGURE 10. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

Typical Performance Curves Unless Otherwise Specified (Continued)

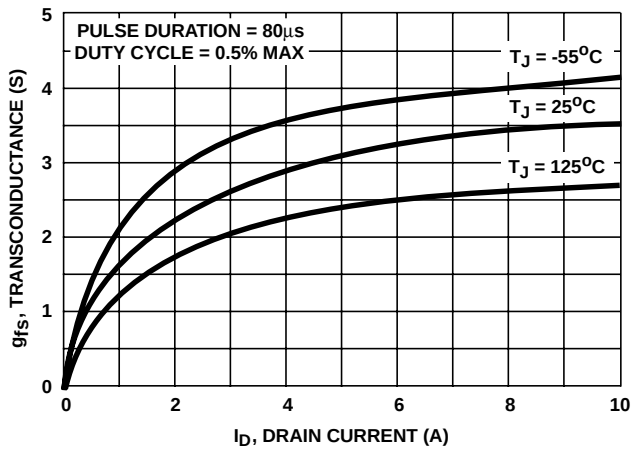


FIGURE 11. TRANSCONDUCTANCE vs DRAIN CURRENT

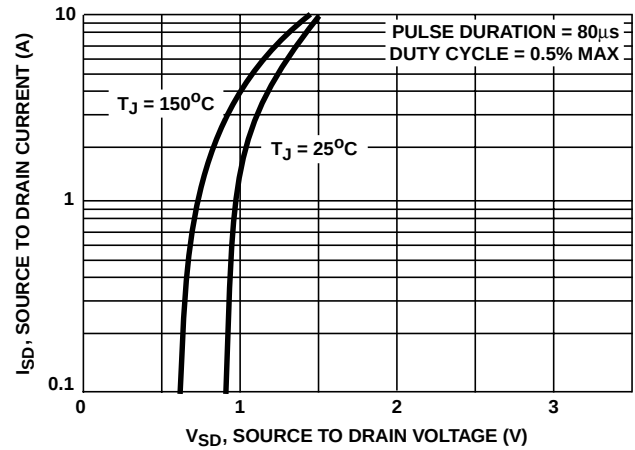


FIGURE 12. SOURCE TO DRAIN DIODE VOLTAGE

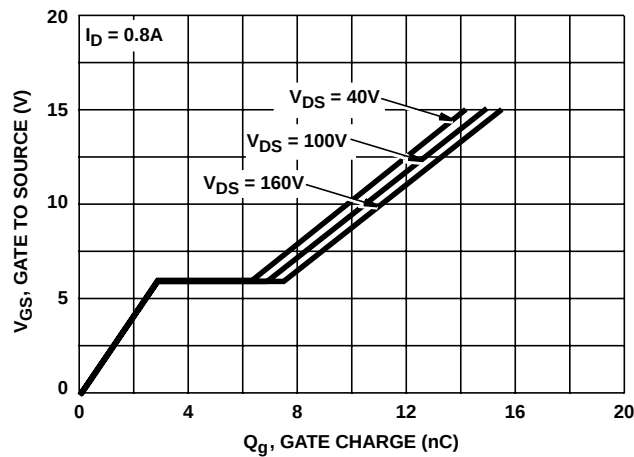


FIGURE 13. GATE TO SOURCE VOLTAGE vs GATE CHARGE

Test Circuits and Waveforms

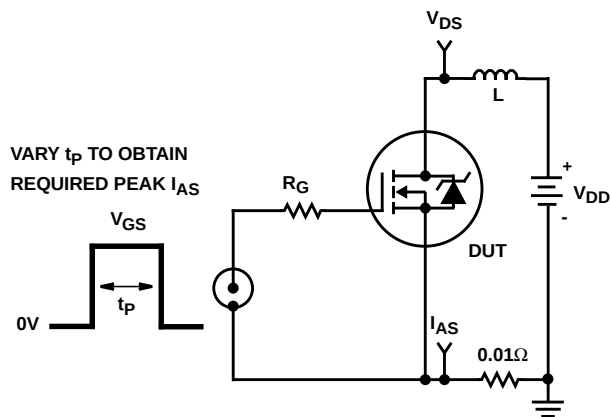


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

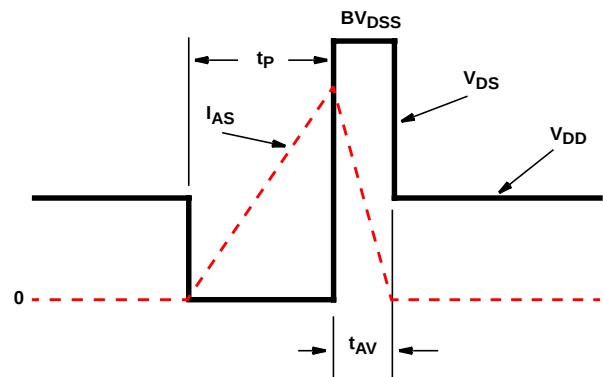


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

Test Circuits and Waveforms (Continued)

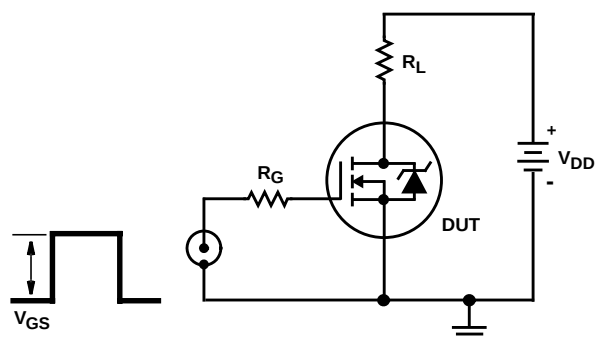


FIGURE 16. SWITCHING TIME TEST CIRCUIT

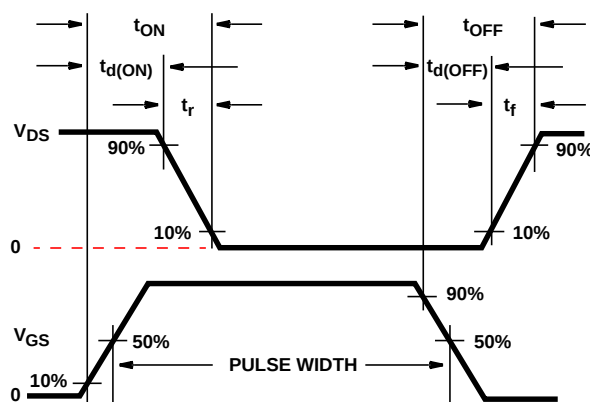


FIGURE 17. RESISTIVE SWITCHING WAVEFORMS

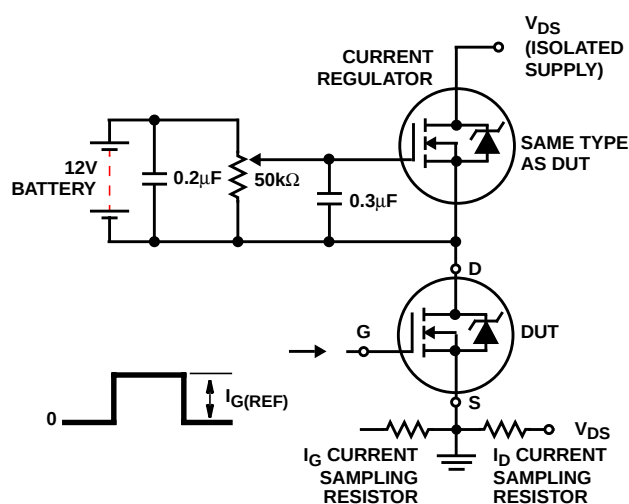


FIGURE 18. GATE CHARGE TEST CIRCUIT

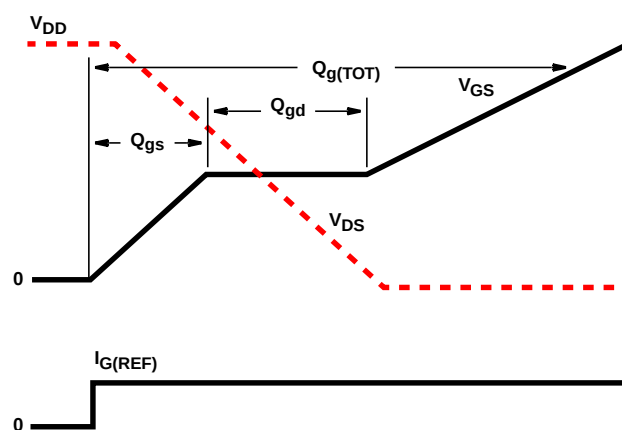


FIGURE 19. GATE CHARGE WAVEFORMS

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